



DESCRIPTION

The AM2301D is available in SOT-23S Package.

B _{VDS}	R _{DS(ON)}		I _D
	-4.5V	-2.5V	
-20V	50mΩ	80 mΩ	-3.7A

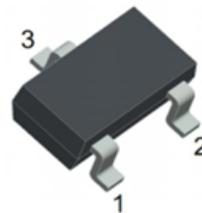
FEATURE

- V_{DS} = -20V, I_D = -3.7A
- Trench FET Power MOSFET
- Ultra Low On-Resistance
- SOT-23S Package.

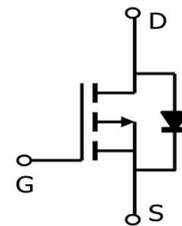
APPLICATION

- Load Switch for Portable Devices
- DC/DC Converter

PIN DESCRIPTION



SOT-23S



ORDERING INFORMATION

Package Type	Part Number	
SOT-23	E3	AM2301DE3R
SPQ: 3,000pcs/Reel		AM2301DE3VR
Note	R: Tape & Reel V: Halogen free Package	
AiT provides all RoHS products		

Pin#	Symbol	Function
1	G	Gate
2	S	Source
3	D	Drain

ABSOLUTE MAXIMUM RATINGS

T_a=25°C Unless otherwise noted

V _{DS} , Drain-Source Voltage	-20V
V _{GS} , Gate-Source Voltage	±12V
I _D , Continuous Drain Current ⁽¹⁾⁽²⁾	-3.7A
I _{DM} , Pulsed Diode Current ⁽³⁾	-22A
P _D , Power Dissipation	1.4W
T _J , Operating Junction	-55°C~+150°C
T _{STG} , Storage Temperature	-55°C~+150°C
R _{θJA} , Thermal Resistance Junction to Ambient (t≤5s)	100°C/W

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**ELECTRICAL CHARACTERISTICS**T_J=25°C, unless otherwise specified.

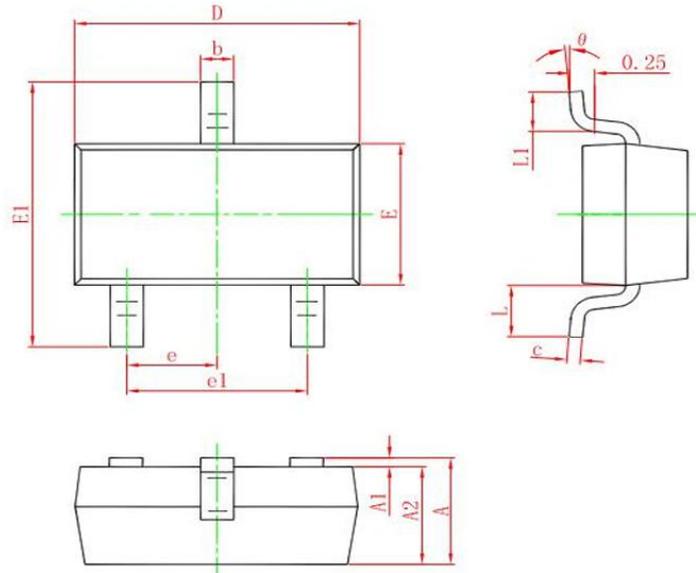
Parameter	Symbol	Conditions	Min	Typ.	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D = -250μA	-20	-	-	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} = -20V, V _{GS} =0V	-	-	-1	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±12V, V _{DS} = 0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D = -250uA	-0.4	-	-1.2	V
Drain-Source On-Static Resistance	R _{DS(on)}	V _{GS} = -4.5V, I _D = -3.7A	-	50	65	mΩ
		V _{GS} = -2.5V, I _D = -3A	-	80	135	
Forward Transconductance	G _{fs}	V _{DS} = -4.5V, I _D = -3.7A	6	-	-	S
Drain Forward Voltage	V _{SD}	V _{GS} =0V, I _S = -1A	-	-0.8	-1.2	V
Continuous Source-Drain Diode Current	I _S	-	-	-	-1.3	A
Dynamic						
Input Capacitance	C _{iss}	V _{DS} = -10V, V _{GS} =0V, f=1MHz	-	633	-	pF
Output Capacitance	C _{oss}		-	145	-	
Reverse Transfer Capacitance	C _{rss}		-	110	-	
Total Gate Charge	Q _g	V _{DS} = -10V, V _{GS} = -4.5V I _D = -3.7A	-	8	-	nC
Gate-Source Charge	Q _{gs}		-	1.2	-	
Gate-Drain Charge	Q _{gd}		-	2.8	-	
Gate Resistance	R _g	f=1MHz	-	6.5	-	Ω
Diode Characteristics						
Body Diode Reverse Recovery Time	T _{rr}	I _F = -3.7A, dI/dt=100A/μs	-	29	-	ns
Body Diode Reverse Recovery Charge	Q _{rr}	I _F = -3.7A, dI/dt=100A/μs	-	11	-	nC
Turn-on Delay Time	t _{d(on)}	V _{DS} = -10V, I _D = -1A, R _L =6Ω, V _{GEN} = -4.5V, R _g =3Ω	-	12	-	ns
Turn-on Rise Time	t _r		-	30	-	
Turn-off Delay Time	t _{d(off)}		-	60	-	
Turn-off Fall Time	t _f		-	50	-	

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t < 5 sec.
3. Pulse Test: Pulse Width≤300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production testing



PACKAGE INFORMATION

Dimension in SOT-23S (Unit: mm)



Symbol	Millimeters (mm)	
	Min.	Max.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950 TYP.	
e1	1.800	2.000
L	0.550 REF.	
L1	0.300	0.500
θ	0°	8°



IMPORTANT NOTICE

AiT Semiconductor Inc. (AiT) reserves the right to make changes to any its product, specifications, to discontinue any integrated circuit product or service without notice, and advises its customers to obtain the latest version of relevant information to verify, before placing orders, that the information being relied on is current.

AiT Semiconductor Inc. integrated circuit products are not designed, intended, authorized, or warranted to be suitable for use in life support applications, devices or systems or other critical applications. Use of AiT products in such applications is understood to be fully at the risk of the customer. As used herein may involve potential risks of death, personal injury, or server property, or environmental damage. In order to minimize risks associated with the customer's applications, the customer should provide adequate design and operating safeguards.

AiT Semiconductor Inc. assumes to no liability to customer product design or application support. AiT warrants the performance of its products of the specifications applicable at the time of sale.